09695715 CLSTITLES

Titles of Most Frequently Occurring Classifications of Patents Returne ${\tt d}$

From A Search of 09695715 on October 25, 2001

3	438/		-	OR, 3 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
		438/689 438/690		CHEMICAL ETCHING .Combined with the removal of material by nonchemical means (e.g., ablating, abradi
ng,	etc.)	438/691		Combined mechanical and chemical material removal
		438/692		Simultaneous (e.g., chemical-mechanical polishing, etc.)
2	330/2		330	OR, 2 XR) : AMPLIFIERS WITH SEMICONDUCTOR AMPLIFYING DEVICE (E.G., TRANSISTOR)
		330/278 330/285		.Including gain control meansHaving particular biasing means
2	340/	Class 340/825	340	OR, 2 XR) : COMMUNICATIONS: ELECTRICAL SELECTIVE .Having indication or alarm (e.g., location indication)
		340/7.2 340/7.58		Code responsive (i.e., paging)Alert
2	342/1			OR, 2 XR) : COMMUNICATIONS: DIRECTIVE RADIO WAVE SYSTEMS AND DEVICES
		342/118 342/128		DETERMINING DISTANCE .With frequency modulation
2	342/1			OR, 1 XR) : COMMUNICATIONS: DIRECTIVE RADIO WAVE SYSTEMS AND DEVICES
		342/175		
2	342/7	70 Class	(1 342	OR, 1 XR) : COMMUNICATIONS: DIRECTIVE RADIO WAVE SYSTEMS AND DEVICES
		342/61 342/70		RETURN SIGNAL CONTROLS EXTERNAL DEVICE .Radar mounted on and controls land vehicle

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)	2		348	: TELEVISION BASIC RECEIVER WITH ADDITIONAL FUNCTION
	2	375/261 Class 375/259	375	: PULSE OR DIGITAL COMMUNICATIONS
		375/260 375/261		.Plural channels for transmission of a single pulse trainQuadrature amplitude modulation
	2	438/424 Class		OR, 0 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
		438/400		FORMATION OF ELECTRICALLY ISOLATED LATERAL SEMICONDUCTIVE STRUCTURE
С		438/424		.Grooved and refilled with deposited dielectri material
	2	438/427 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
		438/400		FORMATION OF ELECTRICALLY ISOLATED LATERAL SEMICONDUCTIVE STRUCTURE
С		438/424		.Grooved and refilled with deposited dielectri
C		438/427		<pre>materialRefilling multiple grooves of different widths or depths</pre>
	2	438/435 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
		438/400		FORMATION OF ELECTRICALLY ISOLATED LATERAL
С		438/424		SEMICONDUCTIVE STRUCTURE .Grooved and refilled with deposited dielectri
		438/435		materialMultiple insulative layers in groove
	2	438/443 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

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	438/400		FORMATION OF ELECTRICALLY ISOLATED LATERAL
	438/439		SEMICONDUCTIVE STRUCTURE .Recessed oxide by localized oxidation (i.e.,
	438/443		LOCOS)Etchback of recessed oxide
2	438/700	(0	OR, 2 XR)
	Class		: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/689 438/694 438/700		CHEMICAL ETCHING .Combined with coating stepFormation of groove or trench
2	438/701 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/689 438/694 438/700 438/701		CHEMICAL ETCHING .Combined with coating stepFormation of groove or trenchTapered configuration
2	438/702 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/689 438/694 438/700 438/702		CHEMICAL ETCHING .Combined with coating stepFormation of groove or trenchPlural coating steps
2	438/792 Class		OR, 2 XR) : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/758		COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR REGION OR OF SEMICONDUCTOR SUBSTRATE
	438/778		.Insulative material deposited upon semiconductive substrate
	438/791 438/792		Silicon nitride formationUtilizing electromagnetic or wave energy
c.)	100, 100		(e.g., photo-induced deposition, plasma, et
2	438/793	(0	OR, 2 XR)
	Class		: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/758		COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR REGION OR OF SEMICONDUCTOR SUBSTRATE
	438/778		.Insulative material deposited upon

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tc.)	438/791 438/792	09695715_CLSTITLES semiconductive substrateSilicon nitride formationUtilizing electromagnetic or wave energy (e.g., photo-induced deposition, plasma, e
((,)	438/793	Organic reactant
2	438/794 Class	(0 OR, 2 XR) 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/758	COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR REGION OR OF SEMICONDUCTOR SUBSTRATE
	438/778	.Insulative material deposited upon semiconductive substrate
	438/791 438/794	Silicon nitride formationOrganic reactant

09695715 CLS

Most Frequently Occurring Classifications of Patents Returned From A Search of 09695715 on October 25, 2001

Original Classifications

- 2 348/554
- 2 438/424

Cross-Reference Classifications

- 3 438/692
- 2 330/285
- 2 340/7.58
- 2 342/128
- 2 438/427
- 2 438/435
- 2 438/443
- 2 438/700
- 2 438/701
- 2 438/702
- 2 438/792
- 2 438/793
- 2 438/794

Combined Classifications

- 3 438/692
- 2 330/285
- 2 340/7.58
- 2 342/128
- 2 342/175
- 2 342/70
- 2 348/554
- 2 375/261
- 2 438/424
- 2 438/427
- 2 438/435
- 2 438/443
- 2 438/700
- 2 438/701
- 2 438/702
- 2 438/792
- 2 438/793
- 2 438/794

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PLUS Search Results for S/N 09695715, Searched October 25, 2001

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